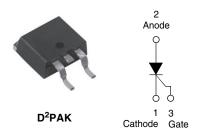


Vishay Semiconductors

# Surface Mountable Phase Control SCR, 16 A



PRODUCT SUMMARY				
V <sub>T</sub> at 10 A	< 1.4 V			
I <sub>TSM</sub>	200 A			
V <sub>RRM</sub>	1600 V			

#### **FEATURES**

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



• Compliant to RoHS directive 2002/95/EC

• Designed and qualified for industrial level

#### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

#### **DESCRIPTION**

The VS-16TTS16SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS							
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5					
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	A				
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5					

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES				
I <sub>T(AV)</sub>	Sinusoidal waveform	10	۸			
I <sub>RMS</sub>		16	A			
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V			
I <sub>TSM</sub>		200	A			
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
T <sub>J</sub>		- 40 to 125	°C			

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-16TTS16SPbF	1600	1600	10					

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Revision: 16-Jul-10

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		
PANAIVIETEN	STINIBUL	TEST CONDITIONS	TYP.	MAX.	UNITS	
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° conduction, half sine wave	1	10		
Maximum RMS on-state current	I <sub>RMS</sub>		1	6	Α	
Maximum peak, one-cycle,	<b>I</b>	10 ms sine pulse, rated V <sub>RRM</sub> applied	1	70		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	2	00		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied		14	A <sup>2</sup> s	
Maximum 1-t for fusing	I <sup>2</sup> τ	10 ms sine pulse, no voltage reapplied		200		
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied		2000		
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25 °C		1.4		
On-state slope resistance	r <sub>t</sub>	T 405 00		24.0		
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C	1.1		V	
Maximum reverse and direct leakage current	1 /1	$T_J = 25 ^{\circ}\text{C}$	0	.5		
waximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$V_R = Rated V_{RRM}/V_{DRM}$	1	0	mA	
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial I <sub>T</sub> = 1 A		150	IIIA	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load	2	00		
Maximum rate of rise of off-state voltage	dV/dt			00	V/µs	
Maximum rate of rise of turned-on current	dl/dt			150		

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P <sub>GM</sub>		8.0	W		
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV		
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α		
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V		
	l <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	90	mA		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60			
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35			
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	3.0			
Maximum required DC gate voltage to trigger	$V_{\mathrm{GT}}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C 2.0		1 ,		
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V		
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detect value	0.25			
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value		mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9			
Typical reverse recovery time	t <sub>rr</sub>	T. – 195 °C	4	μs		
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	110			

## Surface Mountable Phase Control SCR, 16 A

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C		
Soldering temperature	T <sub>S</sub>	For 10 s (1.6 mm from case)	240	1		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.3	°C/W		
Typical thermal resistance, junction to ambient	R <sub>thJA</sub>	PCB mount (1)	40	- 'C/W		
Approximate weight			2	g		
Approximate weight			0.07	OZ.		
Marking device		Case style D <sup>2</sup> PAK (SMD-220)	16TTS	16S		

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

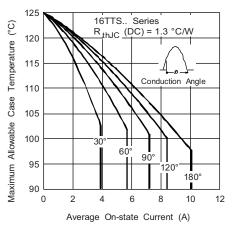


Fig. 1 - Current Rating Characteristics

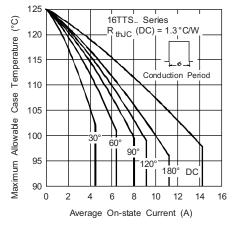


Fig. 2 - Current Rating Characteristics

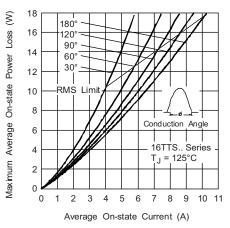


Fig. 3 - On-State Power Loss Characteristics

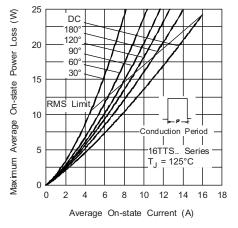


Fig. 4 - On-State Power Loss Characteristics

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## Surface Mountable Phase Control SCR, 16 A



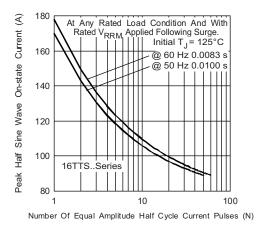


Fig. 5 - Maximum Non-Repetitive Surge Current

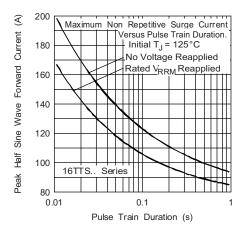


Fig. 6 - Maximum Non-Repetitive Surge Current

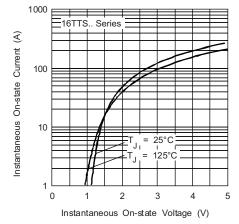


Fig. 7 - On-State Voltage Drop Characteristics

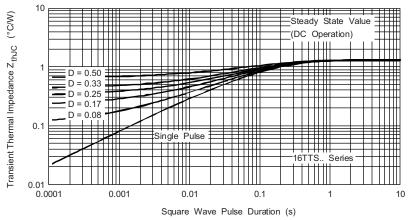


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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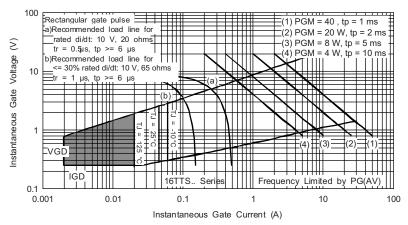
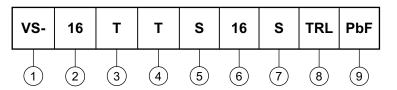


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 HPP product suffix
- 2 Current rating
- 3 Circuit configuration:
  - T = Single thyristor
- 4 Package:
  - T = TO-220AC
- 5 Type of silicon:
  - S = Standard recovery rectifier
- 6 Voltage rating: Voltage code x 100 = V<sub>RRM</sub> (16 = 1600 V)
- **7** S = TO-220 D<sup>2</sup>PAK (SMD-220) version
- 8 • None = Tube
  - TRL = Tape and reel (left oriented)
  - TRR = Tape and reel (right oriented)
- 9 PbF = Lead (Pb)-free

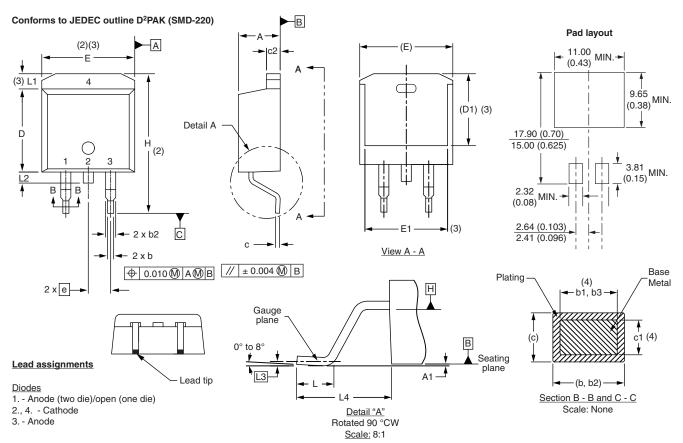
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95046</u>					
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				



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## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	MILLIMETERS INCHES NOTE		INCHES	
STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	1	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

- $^{(1)}$  Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB





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